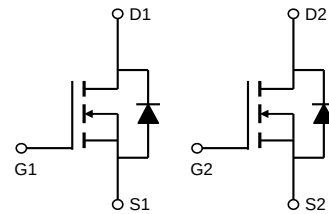
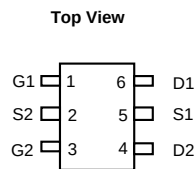
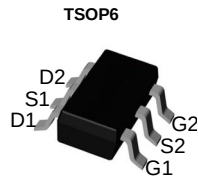


General Description

RST6800 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	3.4A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	=37m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	=39m Ω
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	=44m Ω



Absolute Maximum Ratings T _A =25°C unless otherwise noted					
Parameter		Symbol	Maximum		Units
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	±12		V
Continuous Drain Current	T _A =25°C	I _D	3.4		A
	T _A =70°C		2.7		
Pulsed Drain Current ^C		I _{DM}	20		
Power Dissipation ^B	T _A =25°C	P _D	1.15		W
	T _A =70°C		0.73		
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150		°C
Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	78	110	°C/W
Maximum Junction-to-Ambient ^{A D}	Steady-State		106	150	°C/W
Maximum Junction-to-Lead	Steady-State	R _{θJL}	64	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	1	1.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3.4A T _J =125°C		37 53	43 68	mΩ
		V _{GS} =4.5V, I _D =3A		39	45	mΩ
		V _{GS} =2.5V, I _D =2A		44	60	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3.4A		14		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1	V
I _S	Maximum Body-Diode Continuous Current				1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		235		pF
C _{oss}	Output Capacitance			35		pF
C _{rss}	Reverse Transfer Capacitance			18		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		4.3		Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =3.4A		10		nC
Q _{g(4.5V)}	Total Gate Charge			4.7		nC
Q _{gs}	Gate Source Charge			0.95		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =4.4Ω, R _{GEN} =3Ω		3.5		ns
t _r	Turn-On Rise Time			1.5		ns
t _{D(off)}	Turn-Off DelayTime			17.5		ns
t _f	Turn-Off Fall Time			2.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =3.4A, di/dt=100A/μs		8.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3.4A, di/dt=100A/μs		2.55		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

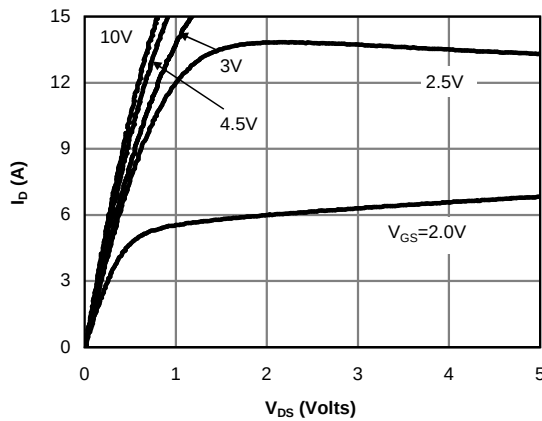


Fig 1: On-Region Characteristics (Note E)

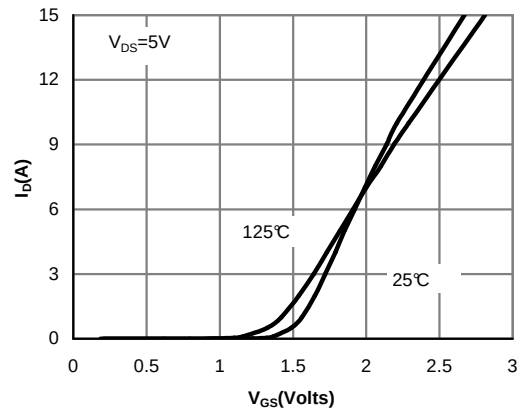


Figure 2: Transfer Characteristics (Note E)

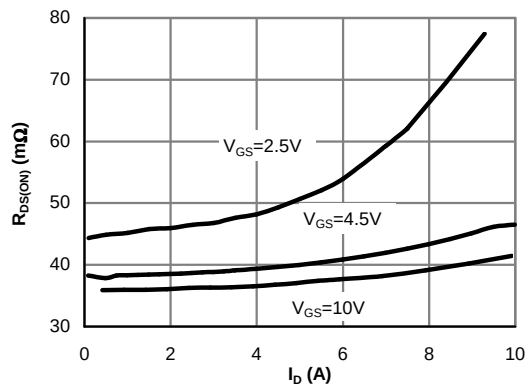


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

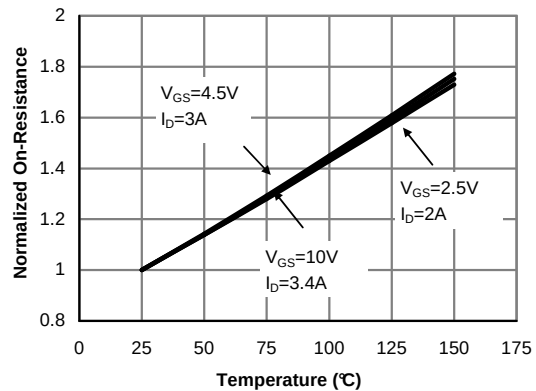


Figure 4: On-Resistance vs. Junction Temperature (Note E)

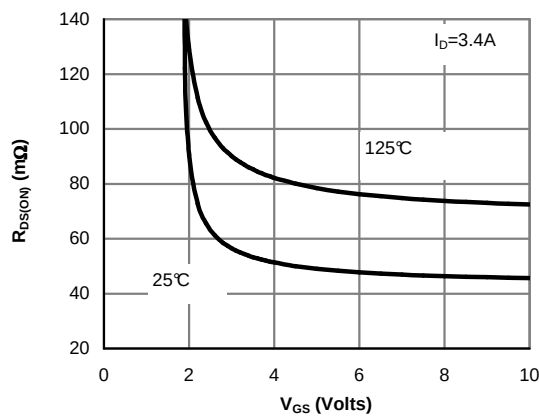


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

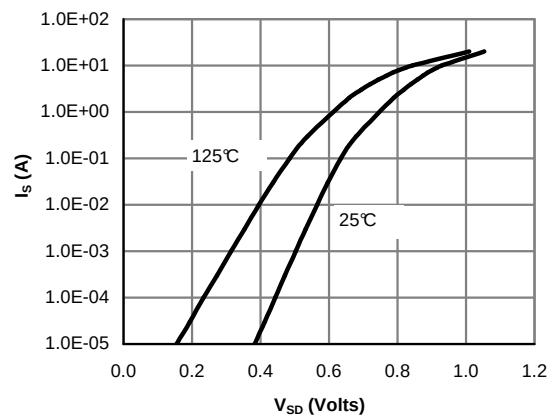


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

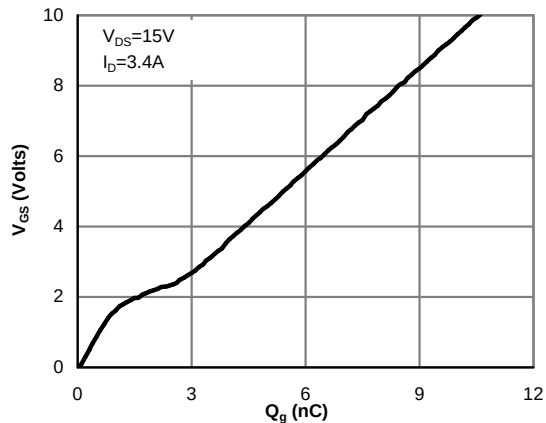


Figure 7: Gate-Charge Characteristics

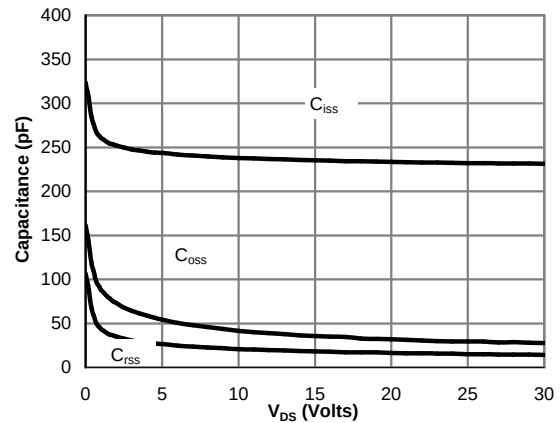


Figure 8: Capacitance Characteristics

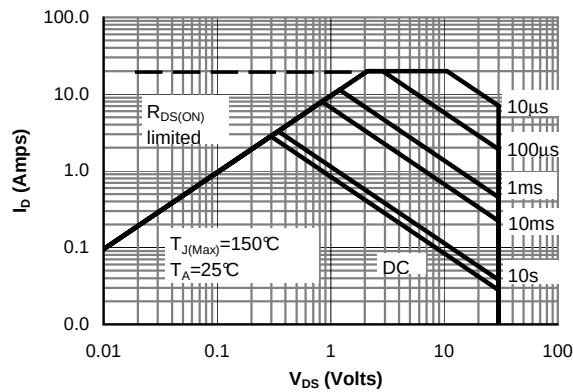


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

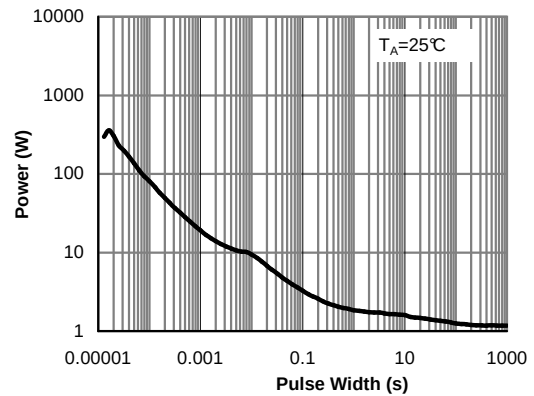


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

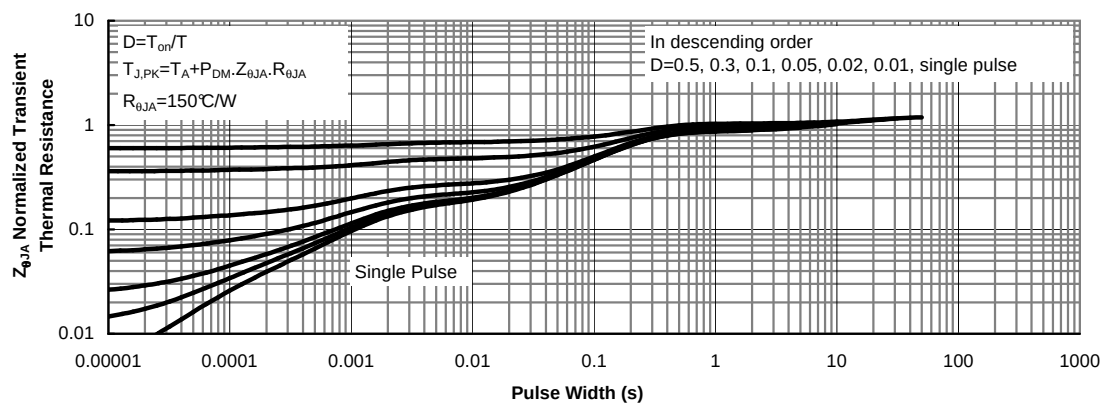
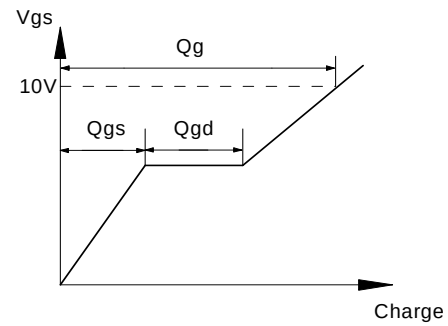
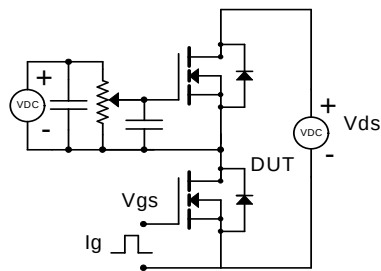
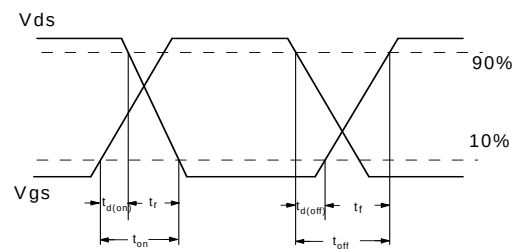
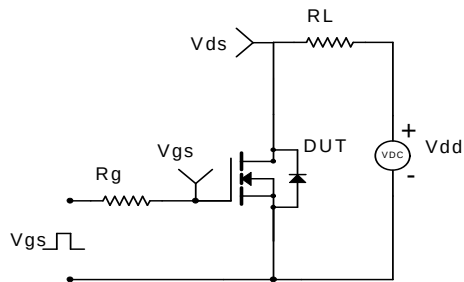


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

